

Emanuele Francesco Pecora

List of Publications by Year in descending order

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32
papers

769
citations

430874

18
h-index

501196

28
g-index

32
all docs

32
docs citations

32
times ranked

1310
citing authors

#	ARTICLE	IF	CITATIONS
1	Antireflection High-Index Metasurfaces Combining Mie and Fabry-Pérot Resonances. ACS Photonics, 2019, 6, 453-459.	6.6	51
2	Broadband Antireflection Coatings Employing Multiresonant Dielectric Metasurfaces. ACS Photonics, 2018, 5, 4456-4462.	6.6	39
3	Deep-Ultraviolet Emitting AlGa _N Multiple Quantum Well Graded-Index Separate-Confinement Heterostructures Grown by MBE on SiC Substrates. IEEE Photonics Journal, 2017, 9, 1-9.	2.0	27
4	Effect of indium in Al _{0.65} Ga _{0.35} N/Al _{0.8} Ga _{0.2} N MQWs for the development of deep-UV laser structures in the form of graded-index separate confinement heterostructure (GRINSCH). Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 1165-1169.	1.8	15
5	Deep-UV optical gain in AlGa _N -based graded-index separate confinement heterostructure. Optical Materials Express, 2015, 5, 809.	3.0	17
6	Photonic-Plasmonic Coupling of GaAs Single Nanowires to Optical Nanoantennas. Nano Letters, 2014, 14, 2271-2278.	9.1	73
7	Size-dependent second-harmonic generation from gold nanoparticles. Physical Review B, 2014, 89, .	3.2	38
8	Enhanced second harmonic generation from InAs nano-wing structures on silicon. Nanoscale, 2013, 5, 10163.	5.6	15
9	Generation of second harmonic radiation from sub-stoichiometric silicon nitride thin films. Applied Physics Letters, 2013, 102, 141114.	3.3	21
10	Development of AlGa _N -based graded-index-separate-confinement-heterostructure deep UV emitters by molecular beam epitaxy. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2013, 31, .	1.2	33
11	Photonic-plasmonic-coupled nanoantennas for polarization-controlled multispectral nanofocusing. Optics Letters, 2013, 38, 4861.	3.3	7
12	Sub-250-nm light emission and optical gain in AlGa _N materials. Journal of Applied Physics, 2013, 113, .	2.5	24
13	Heteroepitaxial Growth of Ge Nanowires on Si Substrates. International Journal of Photoenergy, 2012, 2012, 1-5.	2.5	3
14	Temperature dependence and aging effects on silicon nanowires photoluminescence. Optics Express, 2012, 20, 1483.	3.4	16
15	Rare earth doped Si-rich ZnO for multiband near-infrared light emitting devices. Applied Physics Letters, 2012, 101, 191115.	3.3	27
16	Sub-250 nm room-temperature optical gain from AlGa _N /AlN multiple quantum wells with strong band-structure potential fluctuations. Applied Physics Letters, 2012, 100, 061111.	3.3	52
17	Sub-250nm room temperature optical gain from AlGa _N /AlN multiple quantum wells structures. , 2012, , .		0
18	Generation and Self-Organization of Bimetallic Pd/Au Nanoparticles on SiO ₂ by Sequential Sputtering Depositions and Annealing Processes. Journal of Nanoscience and Nanotechnology, 2012, 12, 8537-8545.	0.9	3

#	ARTICLE	IF	CITATIONS
19	Nanopatterning of silicon nanowires for enhancing visible photoluminescence. <i>Nanoscale</i> , 2012, 4, 2863.	5.6	30
20	Polarization Properties of Deep-Ultraviolet Optical Gain in Al-Rich AlGaN Structures. <i>Applied Physics Express</i> , 2012, 5, 032103.	2.4	13
21	Vertical α - Si -V-Shaped Nanomembranes Epitaxially Grown on a Patterned Si[001] Substrate and Their Enhanced Light Scattering. <i>ACS Nano</i> , 2012, 6, 10982-10991.	14.6	41
22	Ion beam-induced bending of silicon nanowires. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2012, 44, 1074-1077.	2.7	9
23	Nanoscale amorphization, bending and recrystallization in silicon nanowires. <i>Applied Physics A: Materials Science and Processing</i> , 2011, 102, 13-19.	2.3	33
24	Kinetics of Si and Ge nanowires growth through electron beam evaporation. <i>Nanoscale Research Letters</i> , 2011, 6, 162.	5.7	28
25	Influence of O contamination and Au cluster properties on the structural features of Si nanowires. <i>Thin Solid Films</i> , 2010, 518, 2562-2564.	1.8	7
26	Heteroepitaxial Growth and Faceting of Ge Nanowires on Si(111) by Electron-Beam Evaporation. <i>Electrochemical and Solid-State Letters</i> , 2010, 13, K53.	2.2	18
27	Control of growth mechanisms and orientation in epitaxial Si nanowires grown by electron beam evaporation. <i>Nanotechnology</i> , 2009, 20, 135601.	2.6	42
28	Er-based materials for Si microphotronics. <i>Optical Materials</i> , 2009, 31, 1269-1274.	3.6	8
29	Experimental investigations of boron diffusion mechanisms in crystalline and amorphous silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2008, 154-155, 240-246.	3.5	3
30	Indirect Diffusion Mechanism of Boron Atoms in Crystalline and Amorphous Silicon. <i>Materials Research Society Symposia Proceedings</i> , 2008, 1070, 1.	0.1	1
31	Mechanism of Boron Diffusion in Amorphous Silicon. <i>Physical Review Letters</i> , 2008, 100, 155901.	7.8	44
32	Role of the Si excess on the excitation of Er doped SiOx. <i>Applied Physics Letters</i> , 2007, 90, 183102.	3.3	31